

AMENDMENTS TO THE CLAIMS

1. (cancelled)
2. (currently amended) ~~The method of claim 1,~~ A method for etching a silicon on insulator (SOI) substrate, the method comprising:  
opening a hardmask layer formed on an SOI layer of the SOI substrate;  
and  
etching through said SOI layer, a buried insulator layer underneath said SOI layer, and a bulk silicon layer beneath said buried insulator layer using a single etch step, wherein said single etch step is sufficient to etch through said bulk silicon layer to a depth corresponding to a deep trench depth, wherein said etching is implemented with an HBR, NF<sub>3</sub> and O<sub>2</sub> etch chemistry.
3. (original) The method of claim 2, wherein said etch chemistry is applied at a power of about 500 to about 1000 Watts.
4. (currently amended) The method of claim ~~1~~2, wherein said etching is implemented at a pressure of about 10 to about 150 mTorr.
5. (currently amended) The method of claim ~~1~~2, wherein said hardmask layer is formed at a thickness so as to accommodate a 1:1 etch selectivity with respect to said buried insulator layer and about a 5:1 to about a 35:1 etch selectivity with respect to said SOI layer and said bulk silicon layer.
6. (original) The method of claim 5, wherein said hardmask layer further comprises:  
a pad nitride layer formed on said SOI layer; and  
a borosilicate glass (BSG) oxide layer formed on said pad nitride layer.

7. (original) The method of claim 6, wherein said hardmask layer is formed at a thickness of about 6,000 Angstroms to about 20,000 Angstroms.

8. (original) The method of claim 6, wherein said hardmask layer is formed at a thickness of about 10,000 Angstroms to about 18,000 Angstroms.

9. (original) The method of claim 5, wherein said buried insulator layer comprises a buried oxide (BOX) layer formed at a thickness of about 120 to about 140 nanometers.

10. (cancelled)

11. (currently amended) ~~The method of claim 10,~~ A method for forming a deep trench within a silicon on insulator (SOI) substrate, the method comprising:  
forming a hardmask layer on an SOI layer of the SOI substrate;  
patternning a desired deep trench pattern in said hardmask layer; and  
etching through said SOI layer, a buried oxide (BOX) layer underneath said SOI layer, and a bulk silicon layer beneath said BOX layer using a single etch step, wherein said single etch step is sufficient to etch through said bulk silicon layer to a depth corresponding to a deep trench depth, wherein said etching is implemented with an HBR, NF<sub>3</sub> and O<sub>2</sub> etch chemistry.

12. (original) The method of claim 11, wherein said etch chemistry is applied at a power of about 500 to about 1000 Watts.

13. (currently amended) The method of claim ~~10~~11, wherein said etching is implemented at a pressure of about 10 to about 150 mTorr.

14. (currently amended) The method of claim ~~10~~11, wherein said hardmask layer is formed at a thickness so as to accommodate a 1:1 etch selectivity with respect to said BOX layer and about a 5:1 to about a 35:1 etch selectivity with respect to said SOI layer and said bulk silicon layer.

15. (original) The method of claim 14, wherein said hardmask layer further comprises:

a pad nitride layer formed on said SOI layer; and  
a borosilicate glass (BSG) oxide layer formed on said pad nitride layer.

16. (original) The method of claim 15, wherein said hardmask layer is formed at a thickness of about 6,000 Angstroms to about 20,000 Angstroms.

17. (original) The method of claim 15, wherein said hardmask layer is formed at a thickness of about 10,000 Angstroms to about 18,000 Angstroms.

18. (original) The method of claim 13, wherein said buried insulator layer comprises a buried oxide (BOX) layer formed at a thickness of about 120 to about 140 nanometers.